

Electrical characterisation of heavily irradiated microstrip sensors

Thursday 15 November 2012 11:50 (20 minutes)

Electrical characterisation is made of the n-in-p microstrip sensors irradiated by 1 MeV neutron equivalent fluence up to $1E+16$ n/cm². It is shown that the interstrip capacitance is not affected by irradiation and the interstrip resistance remains very high up to the maximum investigated fluence.

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Session Classification: Detector Characterization and Simulations

Track Classification: Full Detector Systems